

Bipolar NPN Bare Die – BTN970

Part Description

The BTN970 is a silicon BJT transistor available in bare die form and well suited for use in High Voltage Driver applications.

Key Parameters:

- VCBO = 600V
- VCEO = 400V
- · VEBO = 7V
- · hFE = 100-200 @ VCE = 10V, IC = 0.02A
- · VCE(Sat) = 0.5V @ IC = 0.05A, IB = 5mA
- · fT = 50 MHz @ VCE = 10V, IE = 0A
- COBO = 7pF @ VCB = 20V

Features

Die Size (Unsawn)

720µm X 720µm, 28 Mils X 28 Mils

This is a shortform datasheet only For the full datasheet

Please contact sales@siliconsupplies.com

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